



# CSD19537Q3T Information



For Reference Only

Part Number CSD19537Q3T

Manufacturer Texas Instruments

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 100V 50A 8VSON

Package 8-PowerVDFN

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **CSD19537Q3T Specifications**

Manufacturer Part Number         CSD19537Q3T           Manufacturer         Texas Instruments           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         8-PowerVDFN           Series         NexFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         100V           Current - Continuous Drain (Id) @ 25°C         50A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         6V, 10V           Vgs(th) (Max) @ Id         3.6V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         21nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1680pF @ 50V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         2.8W (Ta), 83W (Tc)           Rds On (Max) @ Id, Vgs         14.5 mOhm @ 10A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         8-VSON (3.3x3.3)           Package / Case         8-PowerVDFN		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         8-PowerVDFN           Series         NexFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         100V           Current - Continuous Drain (Id) @ 25°C         50A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         6V, 10V           Vgs(th) (Max) @ Id         3.6V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         21nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1680pF @ 50V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         2.8W (Ta), 83W (Tc)           Rds On (Max) @ Id, Vgs         14.5 mOhm @ 10A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         8-VSON (3.3x3.3)           Package / Case         8-PowerVDFN	Manufacturer Part Number	CSD19537Q3T
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FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 50A (Ta) Drive Voltage (Max Rds On, Min Rds On) 6V, 10V Vgs(th) (Max) @ Id 3.6V @ 250µA Gate Charge (Qg) (Max) @ Vgs 21nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1680pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.8W (Ta), 83W (Tc) Rds On (Max) @ Id, Vgs 14.5 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-VSON (3.3x3.3) Package / Case 8-PowerVDFN	Package	8-PowerVDFN
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C50A (Ta)Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id3.6V @ 250μAGate Charge (Qg) (Max) @ Vgs21nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1680pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.8W (Ta), 83W (Tc)Rds On (Max) @ Id, Vgs14.5 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-VSON (3.3x3.3)Package / Case8-PowerVDFN	Series	NexFET?
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Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  6V, 10V  Vgs(th) (Max) @ Id  3.6V @ 250μA  Gate Charge (Qg) (Max) @ Vgs  21nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  1680pF @ 50V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  14.5 mOhm @ 10A, 10V  Operating Temperature  Surface Mount  Supplier Device Package  8-VSON (3.3x3.3)  Package / Case  8-PowerVDFN	Technology	MOSFET (Metal Oxide)
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Vgs(th) (Max) @ Id       3.6V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       21nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1680pF @ 50V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       2.8W (Ta), 83W (Tc)         Rds On (Max) @ Id, Vgs       14.5 mOhm @ 10A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)         Mounting Type       Surface Mount         Supplier Device Package       8-VSON (3.3x3.3)         Package / Case       8-PowerVDFN	Current - Continuous Drain (Id) @ 25°C	50A (Ta)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  14.5 mOhm @ 10A, 10V  Operating Temperature  Operating Type  Surface Mount  Supplier Device Package  8-VSON (3.3x3.3)  Package / Case	Drive Voltage (Max Rds On, Min Rds On)	6V, 10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  14.5 mOhm @ 10A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  8-VSON (3.3x3.3)  Package / Case  8-PowerVDFN	Vgs(th) (Max) @ Id	3.6V @ 250μA
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Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  14.5 mOhm @ 10A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  8-VSON (3.3x3.3)  Package / Case  8-PowerVDFN	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs14.5 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-VSON (3.3x3.3)Package / Case8-PowerVDFN	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  8-VSON (3.3x3.3)  Package / Case  8-PowerVDFN	Power Dissipation (Max)	2.8W (Ta), 83W (Tc)
Mounting Type Surface Mount Supplier Device Package 8-VSON (3.3x3.3) Package / Case 8-PowerVDFN	Rds On (Max) @ Id, Vgs	14.5 mOhm @ 10A, 10V
Supplier Device Package 8-VSON (3.3x3.3) Package / Case 8-PowerVDFN	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-PowerVDFN	Mounting Type	Surface Mount
	Supplier Device Package	8-VSON (3.3x3.3)
Report errors?	Package / Case	8-PowerVDFN
		Report errors?

### CSD19537Q3T Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **CSD19537Q3T Payment Methods**



















# **CSD19537Q3T Shipping Methods**













If you have any question about CSD19537Q3T, please do not hesitate to contact us!

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